

Notice of References Cited	Application/Control No. 10/567,369		Applicant(s)/Patent Under Reexamination ICHINOSE ET AL.	
	Examiner SARAH K. SALERNO		Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Park et al. "Ammonolysis of Ga ₂ O ₃ and its application to the sublimation source for the growth of GaN Film" (2004) Journal of Crystal Growth pp.-6.			
	V	Yang et al. "Preparation and structural properties for FaN films grown on Si (111) by annealing" (2002) Applied Surface Science pp. 254-260.			
	W				
	X				

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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